

Enhanced Solutions

for the World of High Reliability

ANALOG & INTERFACE GUARANTEED RADIATION ASSURED PRODUCTS

September 2000

NSID	SMD	SOURCE OF ELECTRICAL	RAD LEVEL	PKG	RADIATION LIMITS	
					PRE	POST
CLC402AJFQML CLC420AJFQML CLC420AWGFQML	5962F9203301MPA 5962F9175801PA 5962F9175801XA	5962-92033 5962-91758 5962-91758	300k 300k 300k	DIP DIP SOIC	SAME>>>	SAME
DS16F95JFQML DS16F95JFQMLV DS16F95WFQML DS16F95WFQMLV DS16F95WGFQML DS16F95WGFQMLV	5962F8961501QPA 5962F8961501VPA 5962F8961501QHA 5962F8961501VHA 5962F8961501QXA 5962F8961501VXA	5962-89615 5962-89615 5962-89615 5962-89615 5962-89615 5962-89615	300k 300k 300k 300k 300k 300k	DIP DIP FLAT FLAT SOIC SOIC	SAME>>>	SAME
DS26F31MJ-QMLV DS26F31MW-QMLV	5962-7802302VEA 5962-7802302VFA	5962-78023 5962-78023	300k 300k	DIP FLAT	SAME>>>	SAME
DS26F32MER-QML DS26F32MJR-QML DS26F32MJRQMLV DS26F32MWR-QML DS26F32MWRQMLV	5962R7802005Q2A 5962R7802005QEA 5962R7802005VEA 5962R7802005QFA 5962R7802005VFA	5962-78020 5962-78020 5962-78020 5962-78020 5962-78020	100k 100k 100k 100k 100k	LCC DIP DIP FLAT FLAT	SAME>>>	SAME
DS26LS31MEFQML DS26LS31MJFQML DS26LS31MWFQML DS26LS31MJFQMLV DS26LS31MWFQMLV	5962F7802301Q2A 5962F7802301MEA 5962F7802301MFA 5962F7802301VEA 5962F7802301VFA	5962-78023 5962-78023 5962-78023 5962-78023 5962-78023	300k 300k 300k 300k 300k	LCC DIP FLAT DIP FLAT	SAME>>>	SAME
LM101AHRQML LM101AHRQMLV LM101AWRQML LM101AWRQMLV LM101AJRQML LM101AJRQMLV	5962R9951501QGA 5962R9951501VGA 5962R9951501QHA 5962R9951501VHA 5962R9951501QPA 5962R9951501VPA	38510/10103 38510/10103 38510/10103 38510/10103 38510/10103 38510/10103	100k 100k 100k 100k 100k 100k	CAN CAN FLAT FLAT DIP DIP	SAME>>>	SAME
LM111HPQML LM111HPQMLV LM111J-8PQML LM111J-8PQMLV LM111WGPQML LM111WGPQMLV	5962P0052401QGA 5962P0052401VGA 5962P0052401QPA 5962P0052401VPA 5962P0052401QZA 5962P0052401VZA	38510/10304 38510/10304 38510/10304 38510/10304 38510/10304 38510/10304	30k 30k 30k 30k 30k 30k	CAN CAN DIP DIP SOIC SOIC	SAME>>>	SAME

NSID	SMD	SOURCE OF ELECTRICAL	RAD LEVEL	PKG	RADIATION LIMITS		
					PRE	POST	
LM108AHRQML	5962R9863702QGA	38510/10104	100k	CAN	+IIB 2nA	5nA	
LM108AHRQMLV	5962R9863702VGA	38510/10104	100k	CAN	-IIB 2nA	5nA	
LM108AJ-8RQML	5962R9863702QPA	38510/10104	100k	DIP	IIO 0.2nA	0.5nA	
LM108AJ-8RQMLV	5962R9863702VPA	38510/10104	100k	DIP			
LM108AJRQML	5962R9863702QCA	38510/10104	100k	DIP			
LM117HRQML	5962R9951703QXA	38510/11703	100k	CAN	Vout 1.2-1.3V	1.2 - 1.325V	
LM117HRQMLV	5962R9951703VXA	38510/11703	100k	CAN	VRLINE ±9mV RipRej 65dB	±25mV 60mV	
LM117KRQML	5962R9951704QYA	38510/11704	100k	CAN K	Vout 1.2-1.3V	1.2 - 1.325V	
LM117KRQMLV	5962R9951704VYA	38510/11704	100k	CAN K	Vrline ±9mV Vrload ±3.5mV RipRej 65dB	±18mV Vrload ±5.5mV 63B	
LM118HPQML	5962P9853901QGA	38510/10107	30k	CAN	SAME>>>	SAME	
LM118HPQMLV	5962P9853901VGA	38510/10107	30k	CAN			
LM118J-8PQMLV	5962P9853901VPA	38510/10107	30k	DIP			
LM118J-8PQML	5962P9853901QPA	38510/10107	30k	DIP			
LM118WGPQML	5962P9853901QZA	38510/10107	30k	SOIC			
LM118WGPQMLV	5962P9853901VZA	38510/10107	30k	SOIC			
LM124AJRQML	5962R9950401QCA	38510/11006	100k	DIP	VIO ±2mV	±2.2 mV	
LM124AJRQMLV	5962R9950401VCA	38510/11006	100k	DIP	IIO ±10nA	±15nA	
LM124AWGRQML	5962R9950401QZA	38510/11006	100k	SOIC	+IIB 50nA	75nA	
LM124AWGRQMLV	5962R9950401VZA	38510/11006	100k	SOIC	-IIB 50nA	75nA	
LM124AWRQML	5962R9950401QDA	38510/11006	100k	FLAT	AVS 50V/mV	40V/mV	
LM124AWRQMLV	5962R9950401VDA	38510/11006	100k	FLAT			
LM136AH-2.5RQML	5962R0050101QXA	5962-00501	100k	CAN	SAME>>>	SAME	
LM136AH-2.5RQV	5962R0050101VXA	5962-00501	100k	CAN			
LM137KPQML	5962P9951702QYA	38510/11804	30k	CAN K	Delta IADJ +5uA	+ 10uA	
LM137KPQMLV	5962P9951702VYA	38510/11804	30k	CAN K			
LM139AJRQML	5962R9673801QCA	5962-96738	100k	DIP	VIO ±2mV	±2.5mV	
LM139AJRQMLV	5962R9673801VCA	5962-96738	100k	DIP	+IIB 100nA	110nA	
LM139AWGRQML	5962R9673801QXA	5962-96738	100k	SOIC	-IIB 100nA	110nA	
LM139AWGRQMLV	5962R9673801VXA	5962-96738	100k	SOIC	trLH 0.8ns	0.9 ns	
LM139AWRQML	5962R9673801QDA	5962-96738	100k	FLAT			
LM139AWRQMLV	5962R9673801VDA	5962-96738	100k	FLAT			
LM140H-5.0RQML	5962R9955101QXA	38510/10702	100k	CAN	SAME>>>	SAME	
LM140H-5.0RQMLV	5962R9955101VXA	38510/10702	100k	CAN			
LM158AHLQML	5962L8771002QGA	5962-87710	50k	CAN	VIO ±2mV	±4mV	
LM158AHLQMLV	5962L8771002VGA	5962-87710	50k	CAN	+IIB 50nA	60nA	
LM158AJLQML	5962L8771002QPA	5962-87710	50k	DIP	-IIB 50nA	60nA	
LM158AJLQMLV	5962L8771002VPA	5962-87710	50k	DIP			
LM7171AMJRQML	5962R9553601QPA	5962-95536	100k	DIP	SAME>>>	SAME	
LM7171AMJRQMLV	5962R9553601VPA	5962-95536	100k	DIP			
LM7171AMWGRQML	5962R9553601QXA	5962-95536	100k	SOIC			
LM7171AMWGRQMLV	5962R9553601VXA	5962-95536	100k	SOIC			

DEVICES BEING PURSUED


NSID	SMD	SOURCE OF ELECTRICAL	RAD LEVEL	PKG	RADIATION LIMITS	
					PRE	POST
CLC412AJ-QML	5962-9471901QPA	5962-94719		DIP		
CLC414AWG-QML	5962-9169301QXA	5962-91693		SOIC		
CLC520AJ-QML	5962-9164901QCA	5962-91649		DIP		
CLC520AWG-QML	5962-9164901QXA	5962-91649		SOIC		
DS90C031W-QMLV	5962-9583301VFA	5962-95833		FLAT		
DS90C032W-QMLV	5962-9583401QFA	5962-95834		FLAT		
DS90LV031AW-QML		5962-98651		FLAT		
DS90LV031AWGMLS				SOIC		
DS90LV031AWGQML		5962-98651		SOIC		
DS90LV032AW-QML		5962-98652		FLAT		
DS90LV032AWGMLS				SOIC		
DS90LV032AWGQML		5962-98652		SOIC		
LM119JRQML	5962R9679801QCA	5962-96798	100k	DIP	IIB .475uA	1000nA
LM119WRQML	5962R9679801QHA	5962-96798	100k	FLAT	VOS ±3.8mV	±4.0mV
LM119HRQML	5962R9679801QIA	5962-96798	100k	CAN	IOS ±75nA	±150nA
LM119WGRQML	5962R9679801QXA	5962-96798	100k	SOIC		
LM119JRQMLV	5962R9679801VCA	5962-96798	100k	DIP		
LM119WRQMLV	5962R9679801VHA	5962-96798	100k	FLAT		
LM119HRQMLV	5962R9679801VIA	5962-96798	100k	CAN		
LM119WGRQMLV	5962R9679801VXA	5962-96798	100k	SOIC		
LM137HPQML	5962P9951701QXA	38510/11803	30k	CAN	Delta IADJ ±5uA	±20uA
LM137HPQMLV	5962P9951701VXA	38510/11803	30k	CAN		
LM6172AMJRQML	5962R9560401QPA	5962-95604	100k	DIP	SAME>>>	SAME

Notes:

- SMD #'s are preliminary
- Product meets guaranteed levels only after NSC selection process and associated yield losses.
Standard product off-the-shelf is not expected to met these levels.
These devices may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate effect.
Radiation end point limits are guaranteed only for the conditions as specified in MIL-STD-883, Method 1019.5, Condition A.

For more information visit our web site at <http://enhancedsolutions.national.com> or email us at enhanced.solutions@nsc.com

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